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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/766,148	01/27/2004	Yoshihide Senzaki	A-70028-2/MSS/TJH (463035	1972
32940 7	7590 07/13/2006		EXAMINER	
DORSEY &	WHITNEY LLP	CAO, PHAT X		
555 CALIFOR	NIA STREET, SUITE			
SUITE 1000		ART UNIT	PAPER NUMBER	
SAN FRANCI	SCO, CA 94104		2814	

DATE MAILED: 07/13/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

<del></del>		Applica	tion No.	Applicant(s)			
Office Action Summary		10/766	,148	SENZAKI, YOSH	SENZAKI, YOSHIHIDE		
		Examin	er	Art Unit			
		Phat X.		2814			
Period fo	The MAILING DATE of this communor Reply	nication appears on t	he cover sheet	with the correspondence a	ddress		
WHIC - Exte after - If NC - Failu Any	ORTENED STATUTORY PERIOD FOR CHEVER IS LONGER, FROM THE MINIOR OF THE MINIOR OF THE MONTHS FROM THE MINIOR OF THE MONTHS FROM THE MINIOR OF THE MONTHS FROM TH	MAILING DATE OF s of 37 CFR 1.136(a). In no munication. tatutory period will apply and y will, by statute, cause the a	THIS COMMUN event, however, may will expire SIX (6) Mo application to become	IICATION. a reply be timely filed  DNTHS from the mailing date of this ABANDONED (35 U.S.C. § 133).			
Status							
1) 又	Responsive to communication(s) file	ed on 02 May 2006					
2a)□	,	2b)⊠ This action is	non-final				
3)		<i>'</i> —		atters, prosecution as to th	e merits is		
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Dienoeit	·		Ludyto, 1000 o	,			
Disposition of Claims							
4)[2]	Claim(s) <u>1-12</u> is/are pending in the		annidoration				
<b>c</b> \_	4a) Of the above claim(s) is/a	are withdrawn from t	consideration.				
·	Claim(s) is/are allowed.						
· —	Claim(s) <u>1-12</u> is/are rejected.						
7)	Claim(s) is/are objected to.	-4:					
8)	Claim(s) are subject to restri	ction and/or election	requirement.				
Applicat	ion Papers				·		
9)[	The specification is objected to by the	ne Examiner.					
10)	The drawing(s) filed on is/are	: a) accepted or	b)□ objected t	o by the Examiner.			
	Applicant may not request that any object	ection to the drawing(s	) be held in abey	ance. See 37 CFR 1.85(a).			
	Replacement drawing sheet(s) includin	g the correction is requ	uired if the drawir	ng(s) is objected to. See 37 C	CFR 1.121(d).		
11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.							
Priority (	under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  a) All b) Some * c) None of:							
	1. Certified copies of the priority			A I' A! A.I			
	2. Certified copies of the priority				1.04		
	3. Copies of the certified copies	, ,		en received in this Nationa	ii Stage		
	application from the Internation	•		- A			
	See the attached detailed Office action	on for a list of the ce	runea copies no	ot received.			
Attachmer	• •						
1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  4) Interview Summary (PTO-413) Paper No(s)/Mail Date							
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  Paper No(s)/Mail Date  Paper No(s)/Mail Date  Paper No(s)/Mail Date							

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## **DETAILED ACTION**

1. The Request for Continued Examination filed on 5/2/06 is acknowledged.

## Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claims 1-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Steigerwald et al (US. 6,479,404) in view of hegde et al (US. 6,383,873).

Regarding claims 1 and 12, Steigerwald discloses a multilayer gate dielectric film (column 1, lines 61-63) comprising: a first layer formed of Zirconium oxide material (column 7, lines 57-59 and column 8, lines 5-9) having a dielectric constant k and thickness t, the zirconium oxide material having the formula of M(x)O(y) (i.e., ZrO(2)); a second layer formed on top of the first layer, wherein the second layer is formed of zirconium silicate material (column 7, lines 57-59 and column 8, lines 5-9) having a dielectric constant lower than that of the first layer of zirconium oxide material.

Steigerwald does not disclose that the second layer has a thickness smaller than the thickness of the first layer.

However, Hegde (Fig. 5) teaches a multilayer gate dielectric film comprising: a first layer 106 formed of a metal oxide material (column 2, lines 24-34) and having a thickness of 20-80 angstroms (column 2, lines 62-65); and a second layer 108 of a metal silicate material containing metallic element (column 3, lines 21-27) and formed

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on the first layer 106, the second layer 108 having a thickness in the range of one to two atomic layers (column 4, lines 3-4). Accordingly, it would have been obvious to form the second layer having a thickness smaller than the thickness of the first layer because it is desirable to minimize the thickness of the second layer to maintain the high-k characteristics of the composite gate dielectric film, as taught by hegde (column 3, lines 64-66).

Regarding claims 2-3, Steigerwald further discloses that the first layer of metal oxide and the second layer of metal silicate having a dielectric constant of at least about 10 (column 2, lines 51-54).

Regarding claims 4, 6-7 and 9, Steigerwald further discloses that the first layer is ZrO(2) and the second layer is ZrSiO(4) (column 7, lines 57-59).

Regarding claims 5 and 8, Steigerwald further discloses that the metal oxide first layer and the metal silicate second layer include more than one metal element (column 2, lines 51-57).

Regarding claims 10-11, Hegde further teaches that a first layer 106 of metal oxide having a thickness in a range of about 20-80 angstroms (column 2, lines 62-65), and the second layer 108 of metal silicate having a thickness in the range of about one to two atomic layers (column 4, lines 3-4).

## Response to Arguments

4. Applicant's arguments with respect to the claimed invention have been considered but are moot in view of the new ground(s) of rejection. The new references are applied in the new ground of rejection.

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5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Phat X. Cao whose telephone number is 571-272-1703. The examiner can normally be reached on M-F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael Fahmy can be reached on 571-272-1705. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

PC

July 7, 2006

PHAT X. CAO
PRIMARY EXAMINER